

## Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

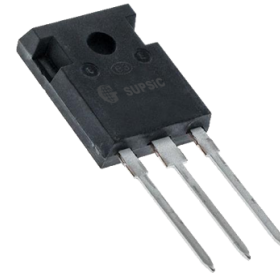
## Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

## Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

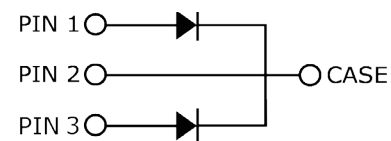
$V_{RRM}$	=	1200 V
$I_F (T_C=135^\circ\text{C})$	=	18 A**
$Q_c$	=	54 nC**



TO-247-3

### Package

Part Number	Package	Marking
GC4D10120D	TO-247-3	GC4D10120



## Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1300	V		
$V_R$	DC Peak Reverse Voltage	1200	V		
$I_F$	Continuous Forward Current (Per Leg/Device)	19/38 9/18 5/10	A	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=160^\circ\text{C}$	Fig. 3
$I_{FRM}$	Repetitive Peak Forward Surge Current	26* 18*	A	$T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_C=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse	
$I_{FSM}$	Non-Repetitive Forward Surge Current	46* 36*	A	$T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_C=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Current	400* 320*	A	$T_C=25^\circ\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse $T_C=110^\circ\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse	Fig. 8
$P_{tot}$	Power Dissipation(Per Leg/Device)	93/187 40/81	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	$V_R=0-650\text{V}$	
$\int i^2 dt$	$i^2t$ value	10.6* 6.5*	A <sup>2</sup> s	$T_C=25^\circ\text{C}$ , $t_p=10$ ms $T_C=110^\circ\text{C}$ , $t_p=10$ ms	
$T_j$	Operating Junction Range	-55 to +175	$^\circ\text{C}$		
$T_{stg}$	Storage Temperature Range	-55 to +135	$^\circ\text{C}$		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

### Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.4 1.9	1.8 3	V	$I_F = 5\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 5\text{ A}$ $T_J = 175^\circ\text{C}$	Fig. 1
$I_R$	Reverse Current	20 40	150 300	$\mu\text{A}$	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	Fig. 2
$Q_C$	Total Capacitive Charge	27		nC	$V_R = 800\text{ V}$ , $I_F = 5\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	390 27 20		pF	$V_R = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 400\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 800\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$	Fig. 6
$E_C$	Capacitance Stored Energy	8.0		$\mu\text{J}$	$V_R = 800\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

### Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.6* 0.8**	$^\circ\text{C}/\text{W}$	Fig. 9

\* Per Leg, \*\* Per Device

### Typical Performance (Per Leg)

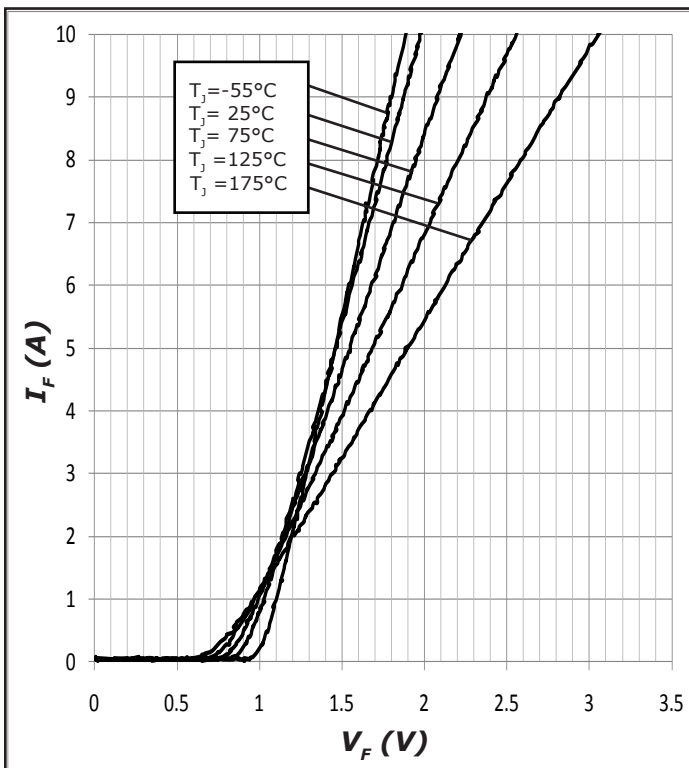


Figure 1. Forward Characteristics

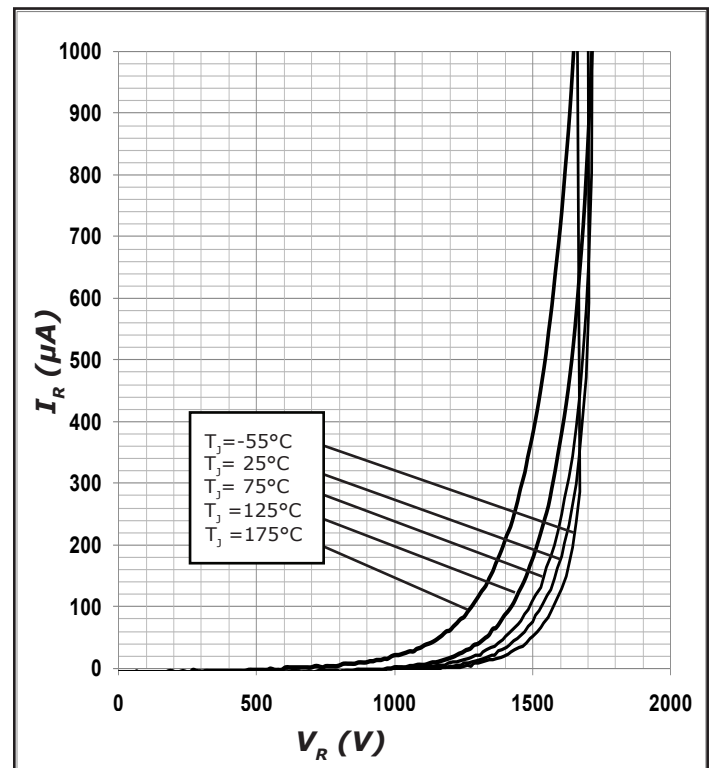


Figure 2. Reverse Characteristics

Typical Performance (Per Leg)

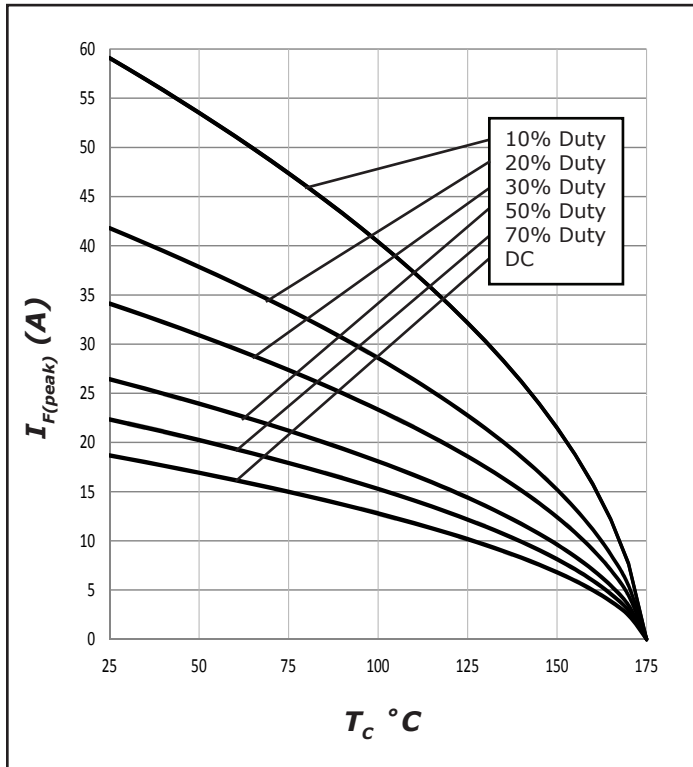


Figure 3. Current Derating

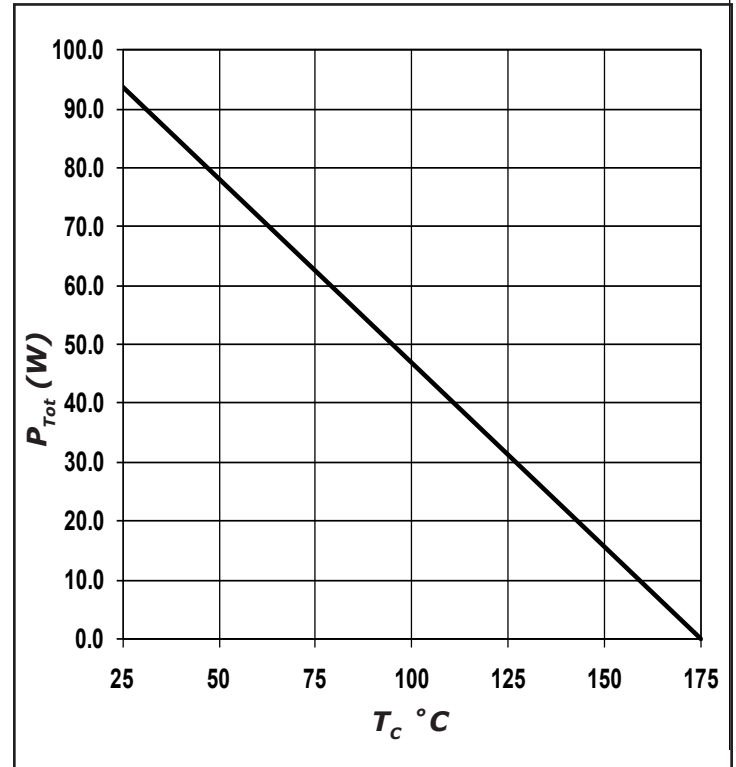


Figure 4. Power Derating

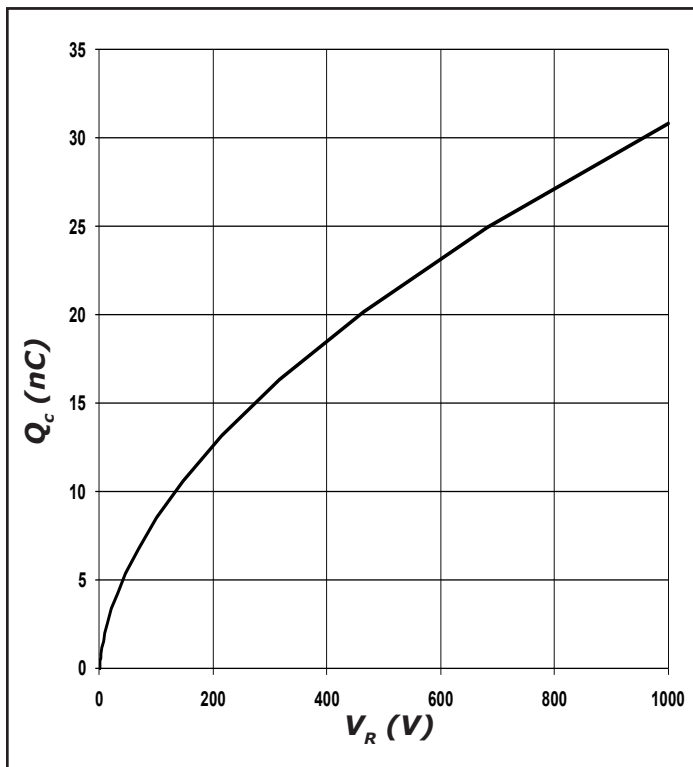


Figure 5. Recovery Charge vs. Reverse Voltage

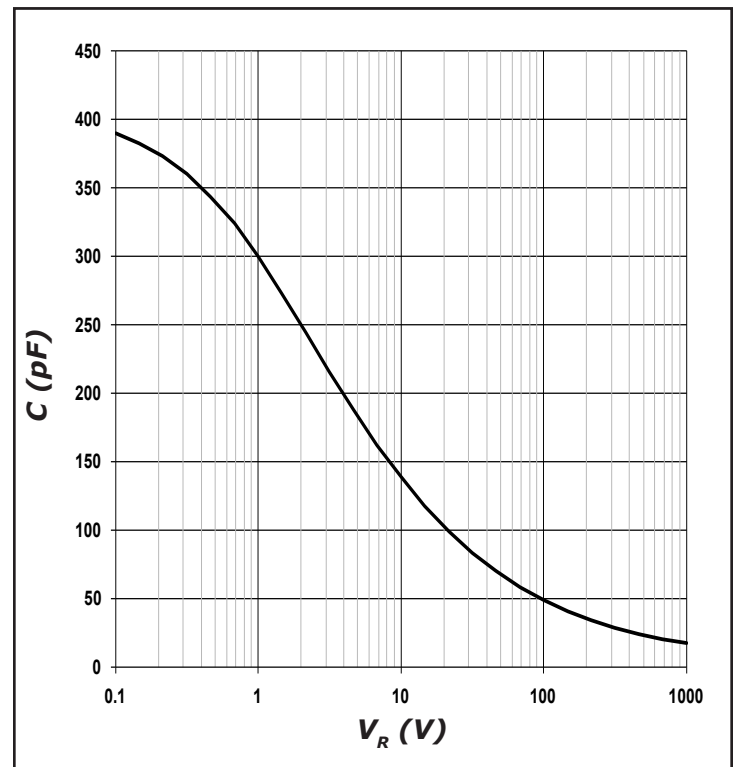


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

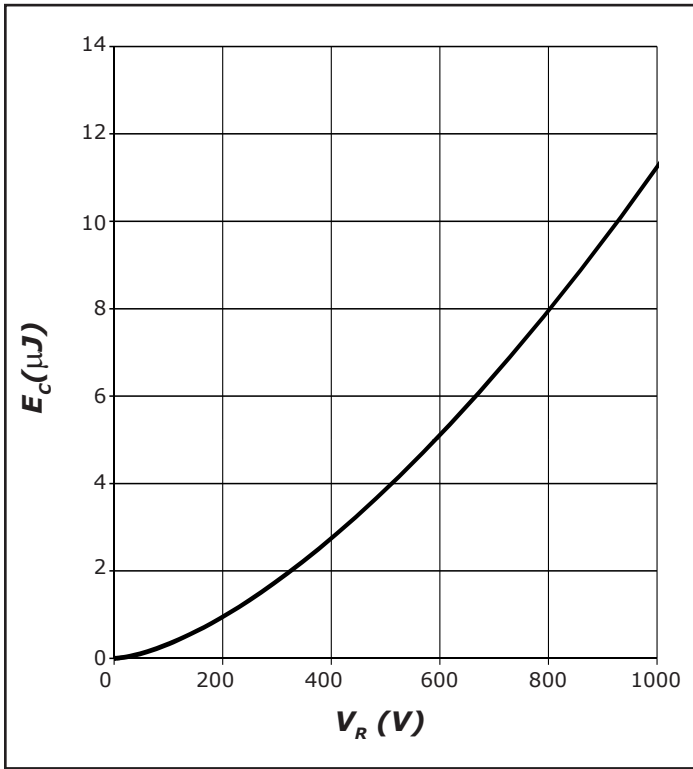


Figure 7. Typical Capacitance Stored Energy, per leg

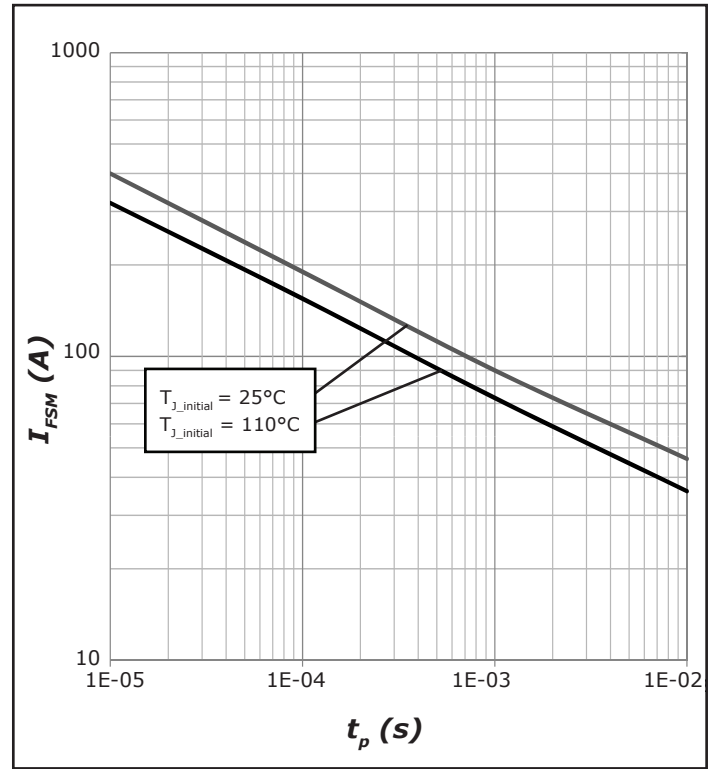


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform), per leg

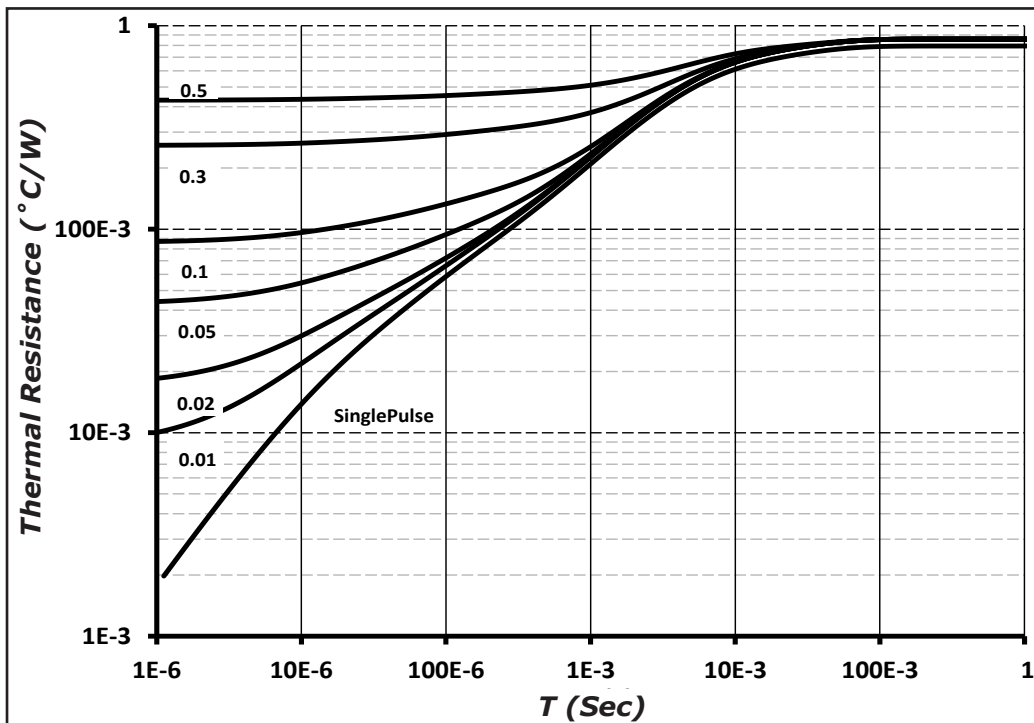
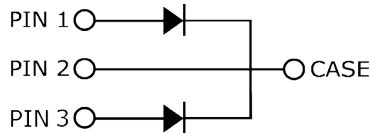
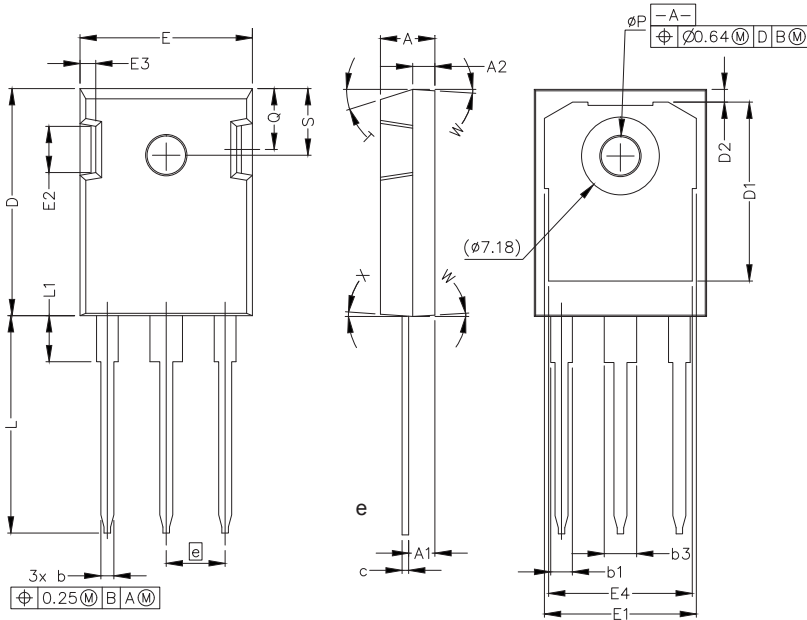


Figure 9. Device Transient Thermal Impedance

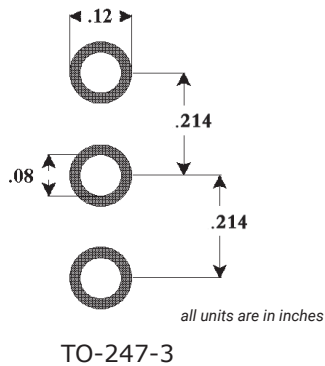
### Package Dimensions

Package TO-247-3



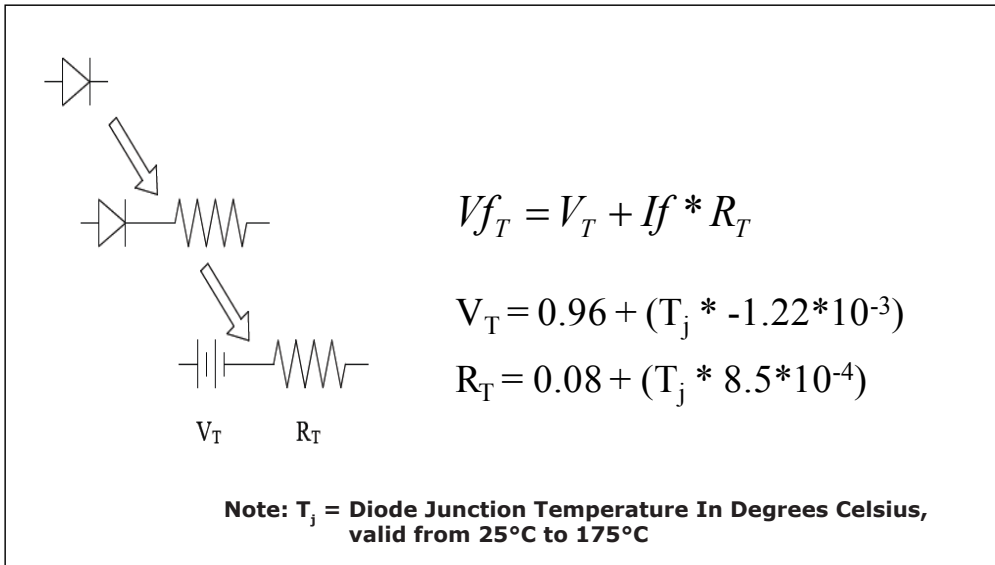
POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b3	.113	.133	2.87	3.38
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
N	3			
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	17.5° REF			
W	3.5° REF			
X	4° REF			

### Recommended Solder Pad Layout



Part Number	Package
GC4D10120D	TO-247-3

**Diode Model**



单击下面可查看定价，库存，交付和生命周期等信息

[>>SUPSiC\(国晶微\)](#)